

9097250 TOSHIBA (DISCRETE/OPTO)

67C 09294 D T-03-09

Silicon Epitaxial Planar Type

Diode

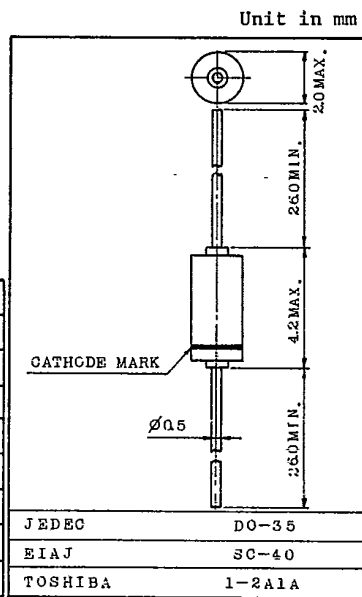
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TENTATIVE

COMMUNICATION AND INDUSTRIAL APPLICATIONS.
HIGH VOLTAGE, ULTRA HIGH SPEED SWITCHING APPLICATIONS.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V _{RM}	85	V
Reverse Voltage	V _R	70	V
Maximum (Peak) Forward Current	I _{FM}	600	mA
Average Forward Current	I _O	200	mA
Surge Current (1 μs)	I _{FSM}	4	A
Power Dissipation	P	500	mW
Junction Temperature	T _j	200	°C
Storage Temperature Range	T _{stg}	-65 ~ 200	°C



Weight : 0.14g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Breakdown Voltage	V _{BR}	I _R =100μA	85	-	-	V
Forward Voltage	V _F (1)	I _F =100μA	0.54	0.60	0.66	V
	V _F (2)	I _F =1mA	0.65	0.71	0.77	V
	V _F (3)	I _F =10mA	0.74	0.80	0.86	V
	V _F (4)	I _F =100mA	0.79	0.86	0.92	V
	V _F (5)	I _F =200mA	0.86	0.93	1.00	V
	V _F (6)	I _F =250mA	-	-	1.10	V
Reverse Current	I _R (1)	V _R =50V	-	-	100	nA
	I _R (2)	V _R =50V, Ta=100°C	-	-	25	μA
	I _R (3)	V _R =70V	-	-	250	nA
Total Capacitance	C _T	V _R =0, f=1MHz	-	-	2.5	pF
Reverse Recovery Time	t _{rr} (1)	I _F =I _R =10mA, I _{rr} =1mA	-	-	6	ns
	t _{rr} (2)	I _F =I _R =10 ~ 200mA I _{rr} =0.1 I _F	-	-	4	ns
	t _{rr} (3)	I _F =I _R =200 ~ 400mA I _{rr} =0.1 I _F	-	-	6	ns

TOSHIBA CORPORATION